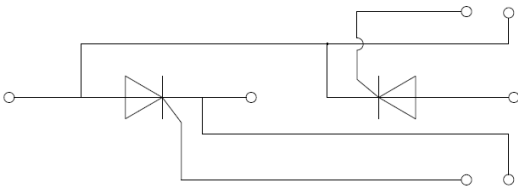




°C		



	°C			
				°C
				°C

[illegible]

			±		

FIG.1: Power dissipation vs. on-state current
(per thyristor or diode)

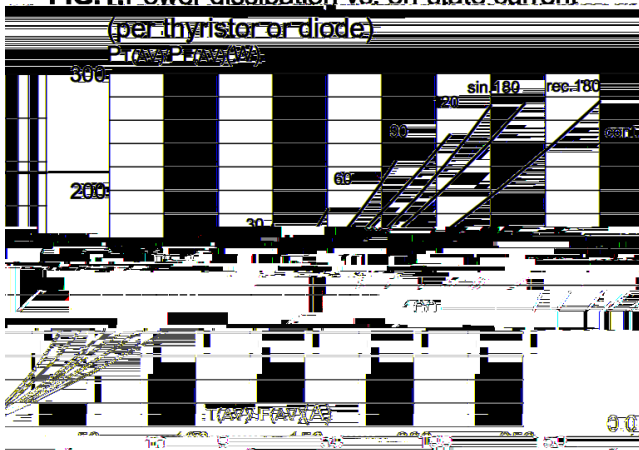


FIG.2: Maximum transient thermal impedance
junction to case (per thyristor or diode)

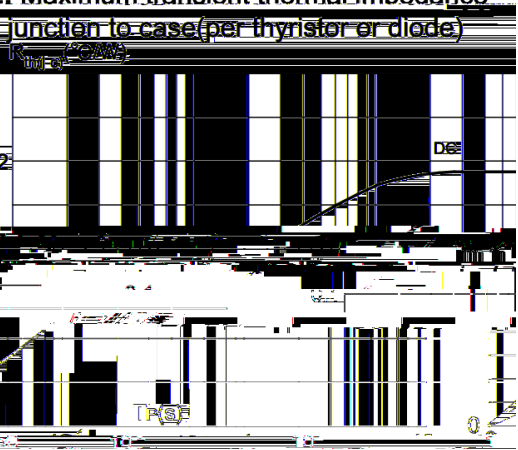


FIG.5 Gate trigger characteristics

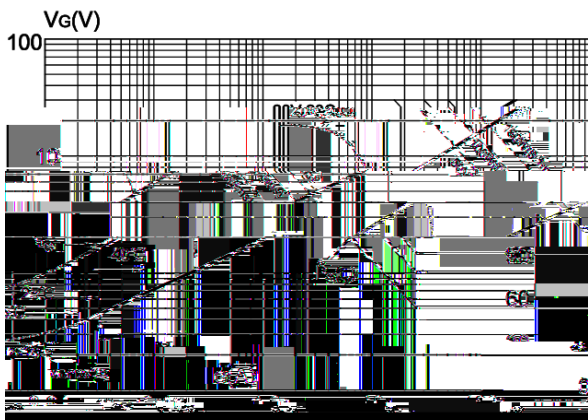


FIG.6: Forward current vs. case temperature
 $I_{F(AV)}$ (per thyristor or diode)

